

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Application of

JOAN WANG

Parent Serial No.: 08/867,229

Parent Filed: June 2, 1997

For: METHOD OF ETCHING HIGH ASPECT
RATIO OPENINGS IN SILICON

PRELIMINARY AMENDMENT

To: Assistant Commissioner for Patents
Washington, DC 20231

Sir:

Please enter the following amendments.

IN THE CLAIMS

Please amend the following claims.

1 (Amended). An etch mixture for silicon [comprising] comprising
essentially of a fluorine-containing gas selected from the group
consisting of SF₆, Si₂F₆ and SiF₄ together with HBr and oxygen.

Cancel claims 7-10.

REMARKS

The claims are 1-6 as amended. An early action on the merits
is respectfully requested.

A clean copy of the claims as amended are set forth on the

Docket No. AM1562D

following page.

Respectfully submitted,

JOAN WANG

By 

Birgit E. Morris

Registration No. 24,484

Birgit E. Morris, Esq
5 Tall Timbers Drive
Princeton, NJ 08540
(609) 921-1695

CLEAN COPY OF THE CLAIMS AS AMENDED

- 1 (Amended). An etch mixture for silicon consisting essentially of a fluorine-containing gas selected from the group consisting of SF_6 , Si_2F_6 and SiF_4 together with HBr and oxygen.
2. An etch mixture according to claim 1 wherein the mixture additionally includes a noble gas.
3. An etch mixture according to claim 1 wherein the mixture contains SF_6 .
4. An etch mixture according to claim 3 wherein the mixture additionally includes Si_2F_6 and SiF_4 .
5. An etch mixture according to claim 3 wherein the volume ratio of HBr: SF_6 is 0.1 to 10.
6. An etch mixture according to claim 3 wherein the volume ratio of HBr and SF_6 : O_2 is 0.1 to 10.